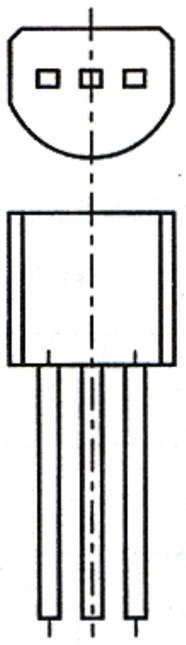
TO-92 Plastic-Encapsulate Transistors

BC369 TRANSISTOR(PNP)



TO-92

1.EMITTER

2.COLLECTOR

3.BASE

FEATURES

Power dissipation

P_{CM}: 0.625W (Tamb=25℃)

Collector current

I_{CM}: -1 A

Collector-base voltage

$V_{(BR)CBO}$: -25 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to + 150℃

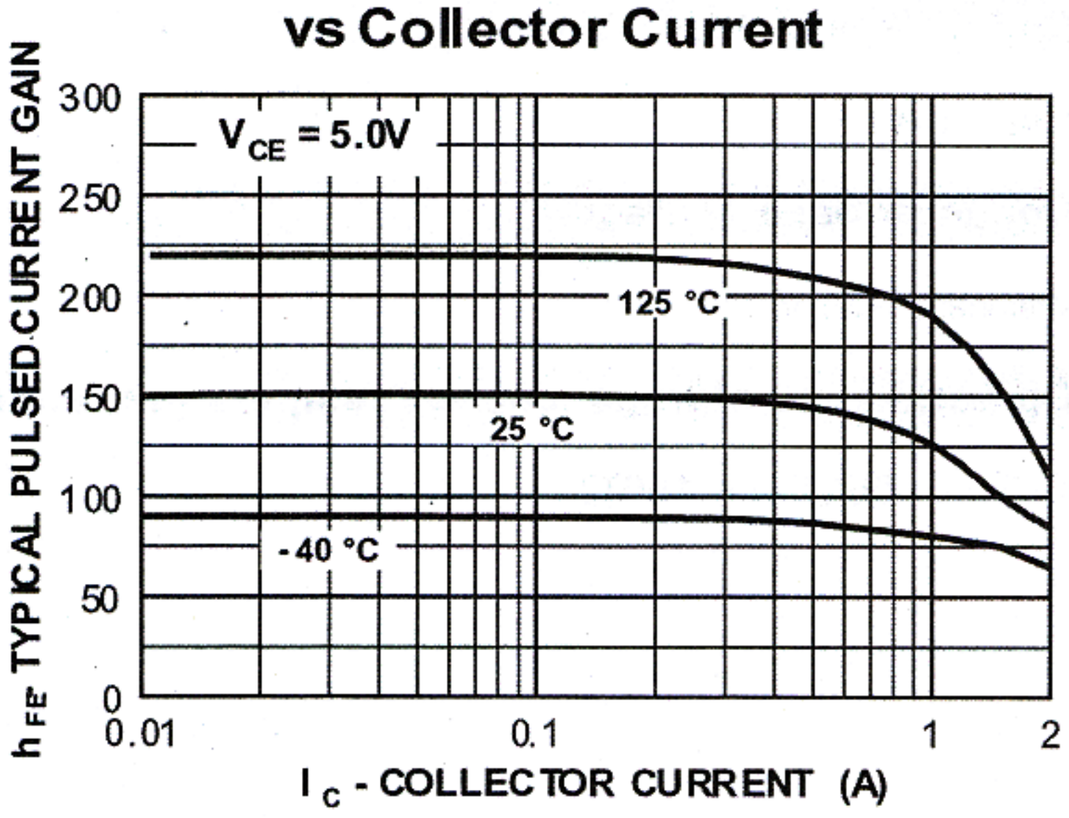
ELECTRICAL CHARACTERISTICS

(Tamb=25℃ unless otherwise specified)

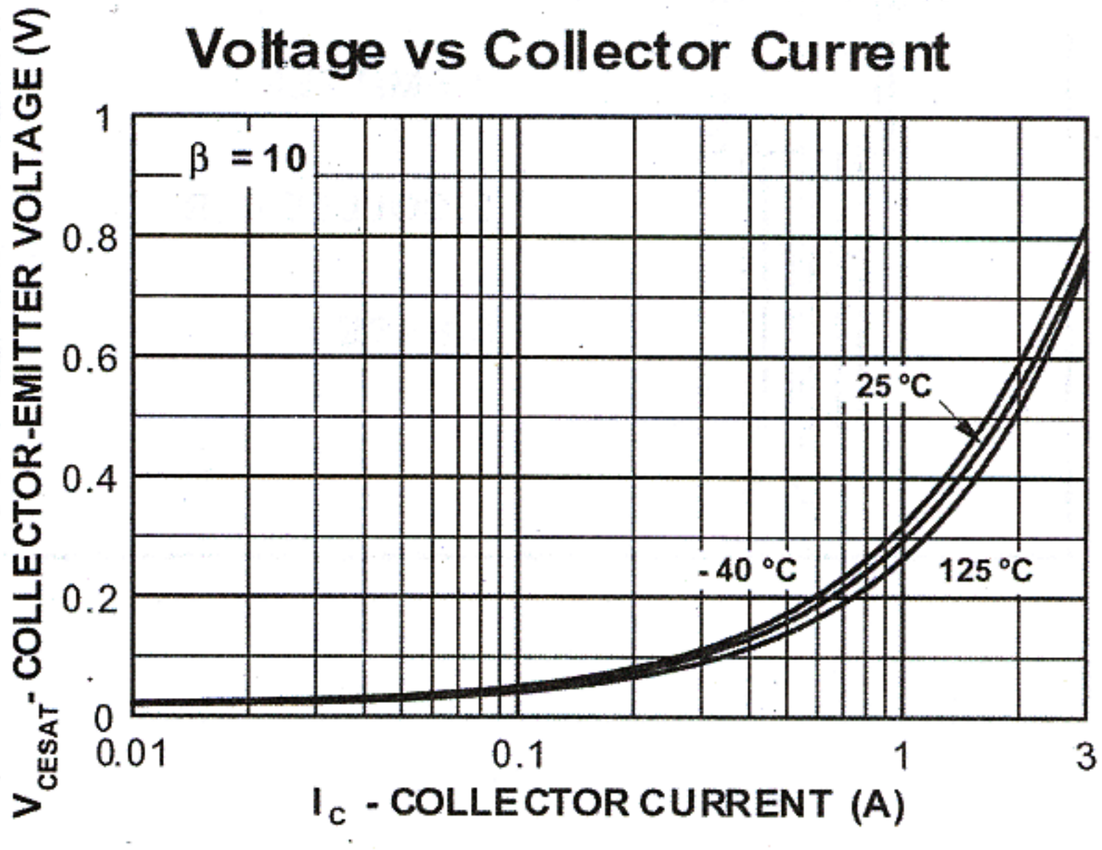
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -100 μ A, I_E=0	-25		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -10 mA, I_B=0	-20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100 μ A, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}= -25 V, I_E=0		-10	μ A
Emitter cut-off current	I_{EBO}	V_{EB}= -5 V, I_C=0		-10	μ A
DC current gain	h_{FE}	V_{CE}= -1 V, I_C= -0.5 mA	85	375	
Base-emitter saturation voltage	V_{CEsat}	I_C= -1 A, I_B= -100 mA		-0.5	V
Base-emitter voltage	V_{BE}	I_C= -1 A, V_{CE}= -1 V		-1	V
Transition frequency	f_T	V_{CE}= -5 V, I_C= -10 mA f =20MHz	65		MHz

Typical Characteristics

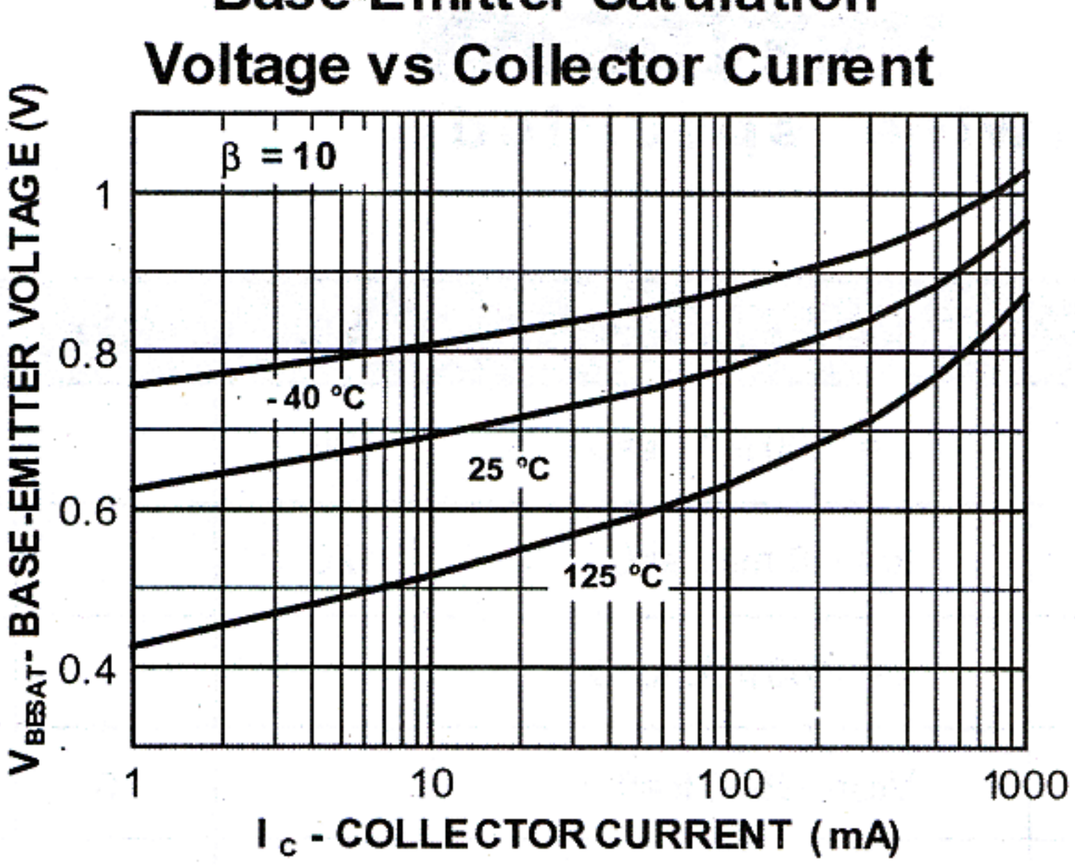
Typical Pulsed Current Gain vs Collector Current



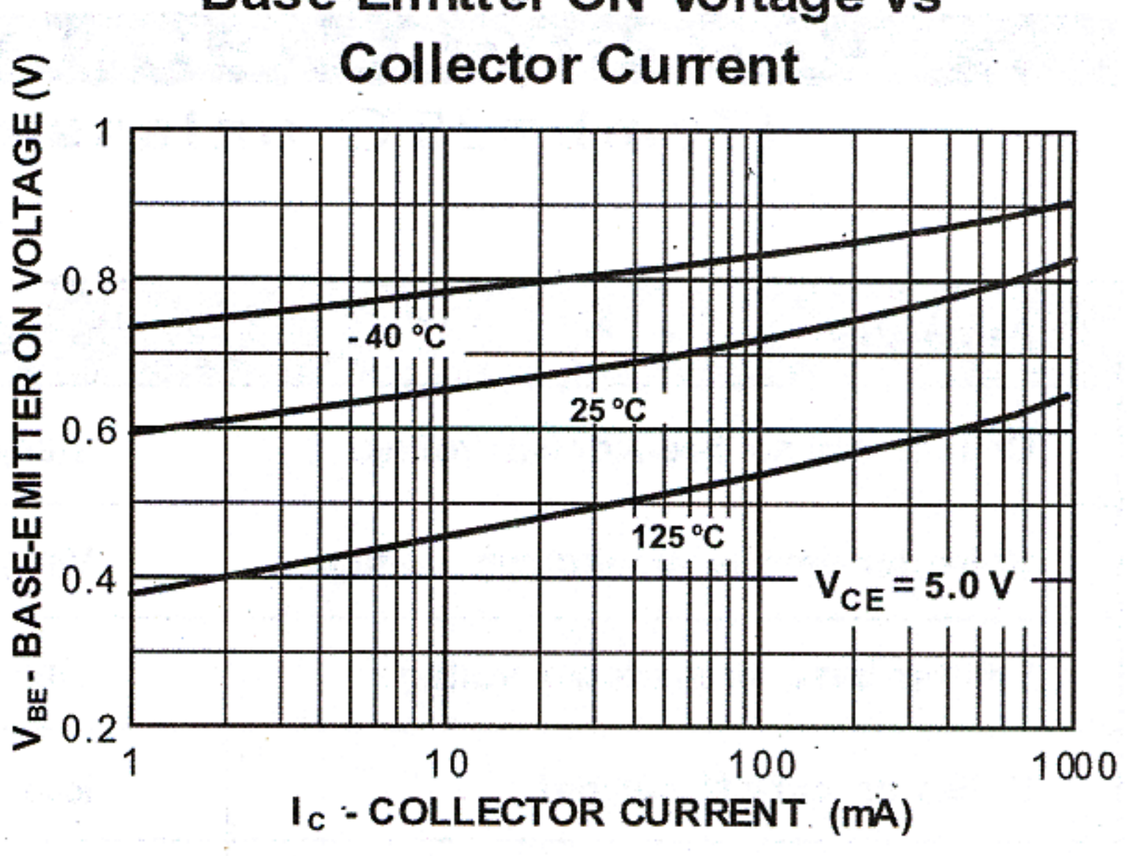
Collector-Emitter Saturation Voltage vs Collector Current



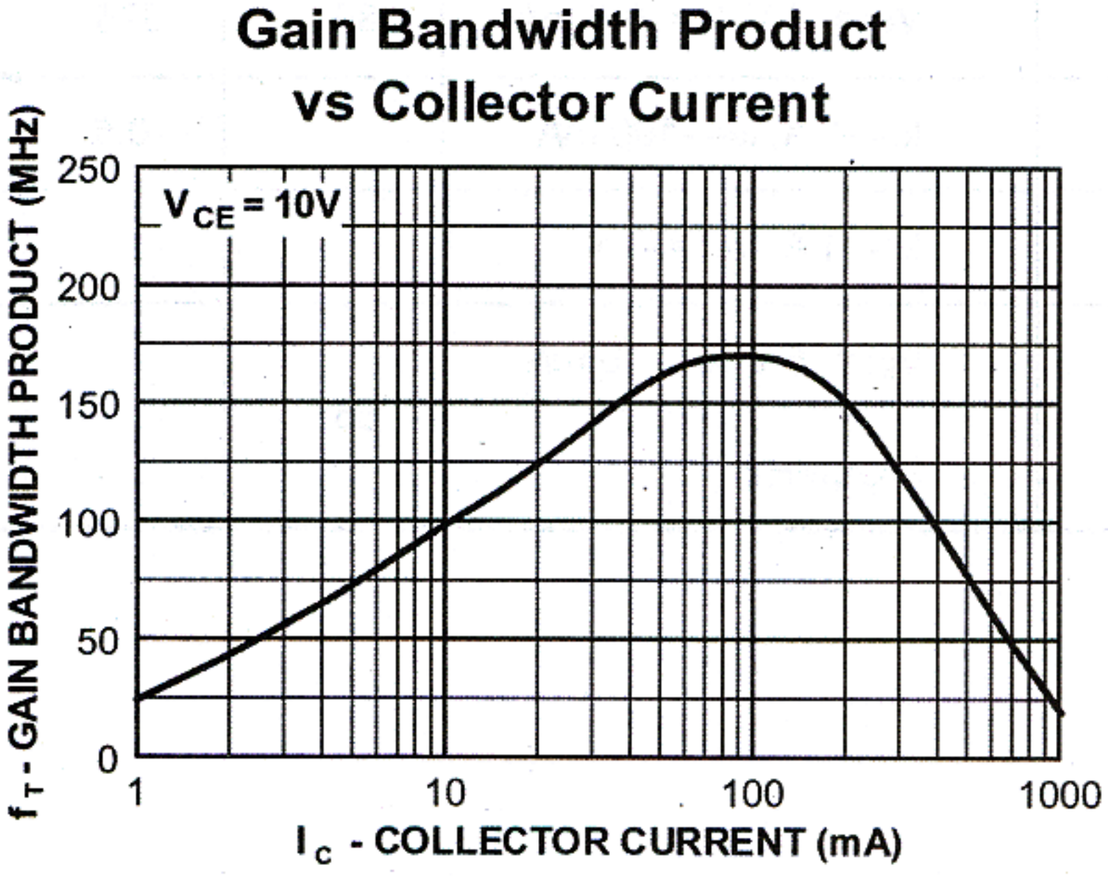
Base-Emitter Saturation Voltage vs Collector Current



Base-Emitter ON Voltage vs Collector Current



Gain Bandwidth Product vs Collector Current



Power Dissipation vs Ambient Temperature